Application No.: 10/777,560 FORM \$70-1449 (Modified) Attorney Docket No.: 108-18.1 LISTS F PATENTS AND PUBLICATIONS FOR Applicant: Harry S. Luan, et al. PARTICANT'S INFORMATION DISCLOSURE Filing Date: February 11, 2004 Group: STATEMENT (Use several sheets if necessary) Page 1 **U.S. PATENT DOCUMENTS** Reference Designation Class Sub-class Filing Date Examiner Initial Document No. Date Name (IF Appropriate) 438 385 6,204,139 3/20/01 Liu et al 438 385 6,531,371 3/11/03 Hsu et al AC ΑD ΑE ΑF AG ΑH ΑĪ ΑJ ΑK AL AM AN AO FOREIGN PATENT DOCUMENTS Class Sub-class Translation Date Document No. (Yes/No) OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.) Zhuang et al., "Novell Colossal Magnetoresistive Thin Film Nonvolatile Resistance Random Access Memory (RRAM)," IEEE 2002. Liu et al., "A New Concept for Non-Volatile Memory: The Electric Pulse Induced Resistive Change Effect in Colossal Magnetoresistive Thin Films," Liu et al., "Electric-pulse-induced reversible resistance change effect in magnetoresistive films," American Institute of Physics, 2000, pg. 2749-2751.

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